



COPY C

Docket No.: 061352-0041

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277 Certificate
Hiroyuki FURUYA, et al. : Confirmation Number: 2093 MAY 31 2005
Application No.: 10/620,432 : Group Art Unit: 2812 of Correction
Patent No. 6,806,109 B2
Filed: July 17, 2003 : Examiner: MULPURI, SAVITRI
Issued: October 19, 2004

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE
AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322

Mail Stop Box 4/ Certificates of Correction
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In reviewing the above-identified patent, a printing error was discovered therein requiring correction in order to conform the Official Record in the application.

The error noted is set forth on the attached copy of form PTO-1050 Rev. 2-93 in the manner required by the Commissioner's Notice.

Specifically, on the title page, side 1, Item "(56)", under "FOREIGN PATENT DOCUMENTS", the Korean reference --KR 2010583 A -- should be inserted. In addition, on side 2 of the title page, at the bottom of the listed "U.S. PATENT DOCUMENTS", the following U.S. Published application data should be inserted -- 2003/0203629 10/2005 Ishibashi et al438/689 --. Copies of the initialed PTO-1449 form listing the Korean application and PTO-892 listing the published application are attached for your information and convenience.

JUN 2 2005

10/620,432

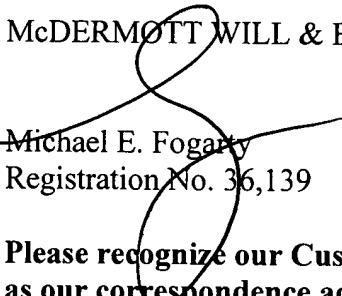
Patent No. 6,806,109 B2

The change requested herein occurred as a result of printing the Letters Patent and the Certificate should be issued without expense under Rule 322 of the Rules of Practice. Accordingly, Applicants request issuance of the Certificate of Correction.

Please charge any shortage in fees due in connection with the filing of this paper to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP


Michael E. Fogarty
Registration No. 36,139

**Please recognize our Customer No. 20277
as our correspondence address.**

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WDC99 1087520-1.061352.0041

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,806,109 B2

DATED : October 19, 2004

INVENTOR(S) : Hiroyuki FURUYA, et al.

It is certified that error appears in the above-identified patent and that said Letter Patent is hereby corrected as shown below:

ON THE TITLE PAGE, side 1,

Item ("56"), under "FOREIGN PATENT DOCUMENTS", insert the following:

-- KR 2010583 A -- ;

ON THE TITLE PAGE, side 2,

Below the listed "U.S. PATENT DOCUMENTS", insert

-- 2003/0203629 10/2005 Ishibashi et al438/689 -- .



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
61352-041SERIAL NO.
10/620,432APPLICANT
Hiroyuki FURUYA, et al.FILING DATE
July 17, 2003GROUP
2812

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
GR		JP 2001-176813 A (w/ English Abstract)	06/29/2001	NICHIA CHEM. IND., LTD.			
		JP 2001-342100 A (w/ partial English translation)	12/11/2001	TOSHIBA CORP.			
		EP 1 278 233 A1 (WO 01/084608)	01/22/2003	TOYODA GOSEI CO., LTD.			
		JP 2001-168042 A (w/ English Abstract)(WO 00/55893)	06/22/2001	MITSUBISHI CABLE IND., LTD.			
		EP 1 184 897 A1	03/06/2000	MITSUBISHI CABLE IND., LTD.			
		JP 2001-93837 A (w/ English Abstract)	04/06/2001	CANON INC.			
		J 2002-353152 A (w/ English Abstract)	12/06/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2002-110569 A (w/ English Abstract)	04/12/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2000-228539 A (w/ English Abstract)	08/15/2000	SHARP CORP.			
		JP 11-191657 (w/ English Abstract)	07/13/1999	NICHIA CHEM. IND., LTD.			
		JP 2001-313259 A		Copy not enclosed.			
		AU 3607601 A		Copy not enclosed.			
		JP 2000-156002 A		Copy not enclosed.			
		JP 2000-331947 A		Copy not enclosed.			
		JP 2000-331937 A		Copy not enclosed.			
		KR 2010583 A		Copy not enclosed.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
GR		I. KIDOGUCHI et al., "Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth", Jpn. J. Appl. Phys., Part 2, Vol. 39, No. 5B, (2000), pages L453-456.	
		S. NAKAMURA, "InGaN/GaN/A1GaN-based laser diodes grown on epitaxially laterally overgrown GaN", Journal of Materials Research, Commentaries and Reviews, Vol. 14, No. 7, July 1999, pages 2716-2731.	
GR		S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN/GaN/A1GaN-Based Laser Diodes Grown on Pure GaN Substrates", Jpn. J. Appl. Phys., Vol. 37, 15 March 1998, pages L309-L312.	

EXAMINER

DATE CONSIDERED

3/9/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

 Notice of References Cited			
MAY 26 2005		Application/Control No. 10/620,432	Applicant(s)/Patent Under Reexamination FURUYA ET AL.
		Examiner Savitri Mulpuri	Art Unit 2812
Page 1 of 2			

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0203629	10-2003	Ishibashi et al.	438/689
*	B	US-6,377,596	04-2002	Tanaka et al.	372/45
*	C	US-2003/0143771	07-2003	Kidoguchi et al.	438/46
*	D	US-2003/0183827	10-2003	Kawaguchi et al.	257/79
*	E	US-6,562,701	05-2003	Ishida et al.	438/479
*	F	US-6,677,173	01-2004	Ota, Hiroyuki	438/22
*	G	US-6,113,685	09-2000	Wang et al.	117/3
*	H	US-2002/0056846	05-2002	Tsuda et al.	257/86
*	I	US-2002/0145148	10-2002	Okuyama et al.	257/88
*	J	US-5,981,977	11-1999	Furukawa et al.	257/94
*	K	US-2002/0182839	12-2002	Ogawa et al.	438/604
*	L	US-2003/0180977	09-2003	Suzuki et al.	438/22
*	M	US-2003/0087467	05-2003	Oohata et al.	438/47

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
*	N	2001217503	08-2001	JP	Kidoguchi	
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages
	U	
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.